Silicon Planar Type

DTA1



1.0A Bidirectional Thyristor

Features

- Low AC power control use.
- Peak OFF-state voltage : 200 to 400V
- RMS ON-state current : 1A
- TO-92 package.

Absolute Maximum Ratings at Ta=25°C				DTA1E	E unit	
Repetitive Peak	V _{DRM}		200	400) V	
OFF-StateVoltage						
RMS ON-State Current	I _{T(RMS)}	Tc=74°C, single-phase	\rightarrow	1.0) A	
		full-wave				
Surge ON-State Current	I _{TSM}	Peak 1 cycle, 50Hz	\rightarrow	8	3 A	
Amperes Squared-Seconds	∫i²T·dt	1ms≤t≤10ms	\rightarrow	0.32	$2 A^2 s$	
Peak Gate Power Dissipation	P _{GM}	f≥50Hz, duty≤10%	\rightarrow	1	l W	
Average Gate Power Dissipation	$P_{G(AV)}$		\rightarrow	0.1	l W	
Peak Gate Current	IGM	f≥50Hz, duty≤10%	\rightarrow	± 0.5	5 A	
Peak Gate Voltage	V _{GM}	f≥50Hz, duty≤10%	\rightarrow	$\pm \epsilon$	5 V	
Junction Temperature	Tj		\rightarrow	125	5 °C	
Strage Temperature	Tstg		_	40 to +125	5 °C	
Weght	-		\rightarrow	0.2	2 g	
Electrical Characteristics a	t Ta=25°C			min tv	vp max	unit
Repetitive Peak	Idrm	$T_i=25^{\circ}C, V_D=V_{DRM}$		-	10) µA
OFF-State Current	DIGH					•
Peak ON-State Voltage	V _{TM}	I _{TM} =1.5A			1.5	5 V
Holding Current	IH	$V_{D}=12V$, gate open			10) mA
Gate Trigger Current* (I)	I _{GT}	$V_{D}=12V, R_{L}=20\Omega$			5	i mA
(II)	I _{GT}	$V_{D}=12V, R_{L}=20\Omega$			5	i mA
(III)	I _{GT}	$V_{D}=12V, R_{L}=20\Omega$]	10	mA
(IV)	I _{GT}	$V_{D}=12V, R_{L}=20\Omega$			5	i mA
Gate Trigger Voltage* (I)	V _{GT}	$V_{\rm D}=12V, R_{\rm L}=20\Omega$			2	2 V
(II)	V _{GT}	$V_{D}=12V, R_{L}=20\Omega$			2	2 V
(III)	V _{GT}	$V_{\rm D}=12V, R_{\rm L}=20\Omega$			2 -	- V
(IV)	V _{GT}	$V_{\rm D}=12V, R_{\rm L}=20\Omega$			2	2 V
Gate Nontrigger Voltage	V _{GD}	$Tc=125^{\circ}C, \overline{V}_{D}=V_{DRM}$		0.2	-	- V
Thermal Resistance	Rth(j-c)	Between junction and case,	AC		40) °C/W

*	:	The	gate	trigger	mode	is	shown	below.

Trigger mode	T2	T1	G
Ι	+	—	+
Ш	+	_	-
Ш	_	+	+
IV	_	+	_



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